

Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claims 19 and 22 without prejudice and accept amended claims 1, 9 and 13 as follows:

1. (Currently Amended) A method of fabricating a semiconductor device comprising:
 - forming a first insulating layer on a substrate;
 - forming an interconnection line within the first insulating layer, wherein the interconnection line functions as a first electrode;
 - forming a second insulating layer on the first insulating layer including the interconnection line;
 - forming an electrode layer and an oxide layer on the second insulating layer;
 - forming a photoresist pattern on the oxide layer;
 - etching the oxide layer and the electrode layer to form a second electrode and an oxide layer pattern stacked over the interconnection line, wherein at least the electrode layer is wet-etched, and the oxide layer is one of wet-etched and dry-etched; and
 - removing the photoresist pattern.
2. (Previously Presented) The method of claim 1, wherein the interconnection line is formed using a damascene technique.

3. (Previously Presented) The method of claim 2, wherein the interconnection line is formed from a copper layer.

4. (Previously Presented) The method of claim 1, wherein the second insulating layer is formed of a dielectric layer.

5. (Original) The method of claim 4, wherein the dielectric layer is formed of one of a silicon nitride layer, a silicon carbide layer, a silicon oxycarbide layer and a silicon carbonitride layer.

6. (Original) The method of claim 1, wherein the electrode layer is formed of one of a tantalum layer, a tantalum nitride layer, a titanium layer and a titanium nitride layer.

7. (Original) The method of claim 1, wherein etching is performed using a mixture of hydrofluoric acid and nitric acid.

8. (Original) The method of claim 1, wherein the electrode layer is formed of one of a tungsten layer and a tungsten nitride layer.

9. (Currently Amended) The method of claim 1, wherein ~~the oxide layer is one of wet-etched and dry-etched,~~ and the electrode layer is wet-etched using hydrogen peroxide.

10. (Original) The method of claim 1, further comprising using the photoresist pattern as an etching mask.

11. (Original) The method of claim 1, wherein the electrode layer is formed from metal.

12. (Original) The method of claim 1, wherein the interconnection line is formed from metal.

13. (Currently Amended) A method of fabricating a semiconductor device comprising:

forming a first insulating layer on a substrate;

forming an interconnection line within the first insulating layer, wherein the interconnection line functions as a first electrode;

forming a second insulating layer on the first insulating layer including the interconnection line;

forming an electrode layer on the second insulating layer;

forming a photoresist pattern on the electrode layer; [[and]]

wet-etching the electrode layer to form a second electrode;

forming an oxide layer on the electrode layer; and

one of wet-etching and dry-etching the oxide layer.

14. (Original) The method of claim 13, wherein the interconnection line is formed from metal.

15. (Previously Presented) The method of claim 13, wherein the interconnection line is formed from copper using a damascene process.

16. (Previously Presented) The method of claim 13, wherein the second insulating layer is a dielectric layer formed of one of a silicon nitride layer, a silicon carbide layer, a silicon oxycarbide layer and a silicon carbonitride layer.

17. (Original) The method of claim 13, wherein the electrode layer is formed of one of a tantalum layer, a tantalum nitride layer, a titanium layer, a titanium nitride layer, a tungsten layer and a tungsten nitride layer.

18. (Original) The method of claim 13, wherein the electrode layer is wet-etched using one of hydrogen peroxide and a mixture of hydrofluoric acid and nitric acid.

19. (Canceled)

20. (Original) The method of claim 13, further comprising removing the photoresist pattern.

21. (Original) The method of claim 13, wherein the electrode layer is formed from metal.

22. (canceled)